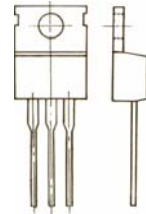


**TO-220 Plastic-Encapsulate Transistors****2SB1375** TRANSISTOR (PNP)**FEATURES**

- High Power Dissipation: $P_C=25W(T_C=25^{\circ}C)$
- Low voltage: $V_{CE(sat)}=-1.5V(Max)(I_C=-2A, I_B=-0.2A)$
- Collector metal(Fin)is Coverd with Mold Regin
- Complementary to 2SD2012

TO-220

1. BASE
2. COLLECTOR
3. EMITTER



1 2 3

MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Dissipation	2	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-50mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-7V, I_C=0$			-10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-0.5A$	100		320	
	$h_{FE(2)}$	$V_{CE}=-5V, I_C=-2A$	15			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5V, I_C=-0.5A$			-1	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-0.5A$		9		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		50		pF

Typical Characteristics

2SB1375

